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**NATIONAL STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

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**Semiconductor devices -- Discrete devices -- Part 9:
Insulated-gate bipolar transistors (IGBT)**

半导体器件 分立器件 第9部分：绝缘栅双极晶体管(IGBT)
(English Translation)

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What this standard covers

This standard specifies the insulated gate bipolar transistor (IGBT) terminology, text symbols, essential ratings and characteristics and test methods, product-specific requirements.

Document data

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Standards quoted by this document

IEC 60747-1-2006; IEC 60747-2; IEC 60747-6; IEC 61340-2-1; IEC 61340-2-3; IEC 61340-3-1; IEC 61340-3-2; IEC 61340-4-10; IEC 61340-4-1; IEC 61340-4-3; IEC 61340-4-4; IEC 61340-4-5; IEC 61340-4-6; IEC 61340-4-7; IEC 61340-4-8; IEC 61340-4-9; IEC 61340-5-1